



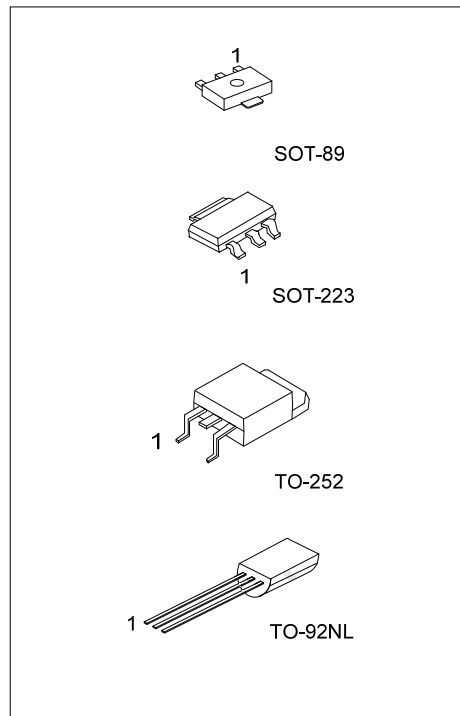
2SA1797

PNP SILICON TRANSISTOR

POWER TRANSISTOR

FEATURES

- * Low Saturation Voltage.
 $V_{CE(SAT)} = -0.35V(\text{Max})$ at $I_C / I_B = -1A / -50mA$
- * Excellent DC Current Gain Characteristics



ORDERING INFORMATION

Ordering Number			Package	Pin Assignment			Packing
Normal	Lead Free Plating	Halogen Free		1	2	3	
2SA1797-x-AA3-R	2SA1797L-x-AA3-R	2SA1797G-x-AA3-R	SOT-223	B	C	E	Tape Reel
2SA1797-x-AB3-R	2SA1797L-x-AB3-R	2SA1797G-x-AB3-R	SOT-89	B	C	E	Tape Reel
2SA1797-x-T9N-B	2SA1797L-x-T9N-B	2SA1797G-x-T9N-B	TO-92NL	E	C	B	Tape Box
2SA1797-x-T9N-K	2SA1797L-x-T9N-K	2SA1797G-x-T9N-K	TO-92NL	E	C	B	Bulk
2SA1797-x-TN3-R	2SA1797L-x-TN3-R	2SA1797G-x-TN3-R	TO-252	B	C	E	Tape Reel
2SA1797-x-TN3-T	2SA1797L-x-TN3-T	2SA1797G-x-TN3-T	TO-252	B	C	E	Tube

<p>2SA1797L-x-AA3-R</p> <p>(1) Packing Type (2) Package Type (3) Rank (4) Lead Free</p>	<p>(1) R: Tape Reel, B: Tape Box, T: Tube, K: Bulk (2) AA3: SOT-223, AB3: SOT-89, T9N: TO-92NL, TN3: TO-252 (3) refer to Classification of h_{FE} (4) L: Lead Free Plating, Blank: Pb/Sn, G: Halogen Free</p>
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■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	-50	V
Collector-Emitter Voltage		V_{CEO}	-50	V
Emitter-Base Voltage		V_{EBO}	-6	V
Collector Current	DC	I_C	-2	A
	PULSE(Note 1)		-5	A
Collector Power Dissipation	TO-92NL	P_C	1	W
	SOT-223		0.8	W
	SOT-89		0.5	W
	TO-252		1.9	W
Junction Temperature		T_J	150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Note: 1. Single pulse, $P_W=10ms$

2. Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

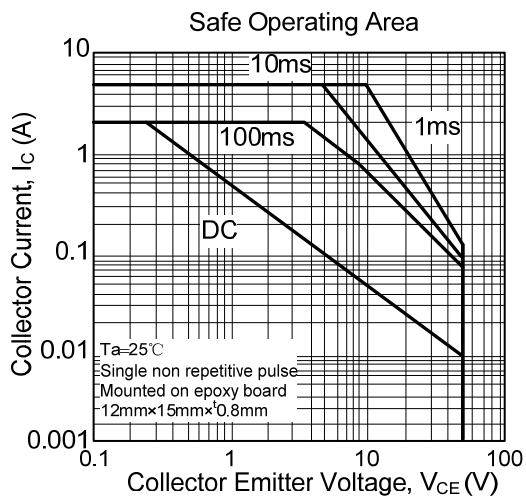
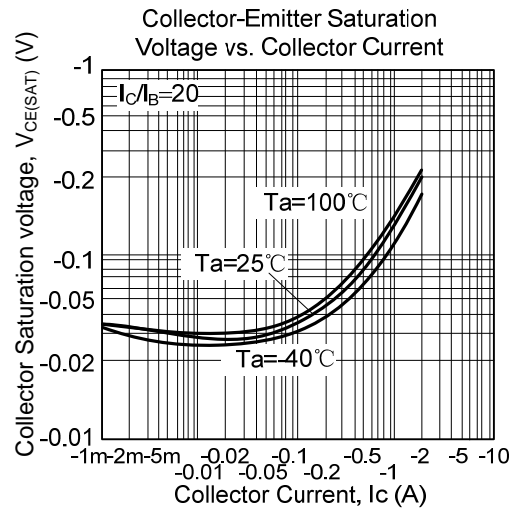
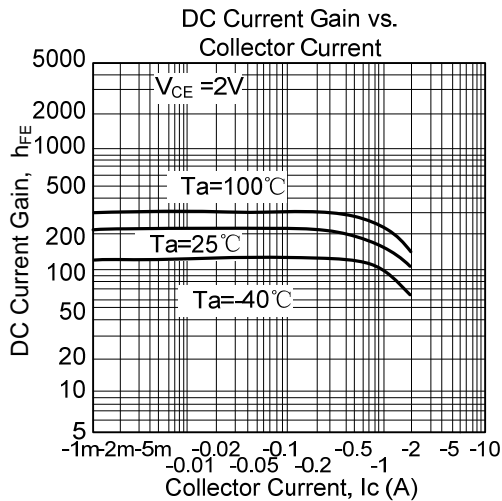
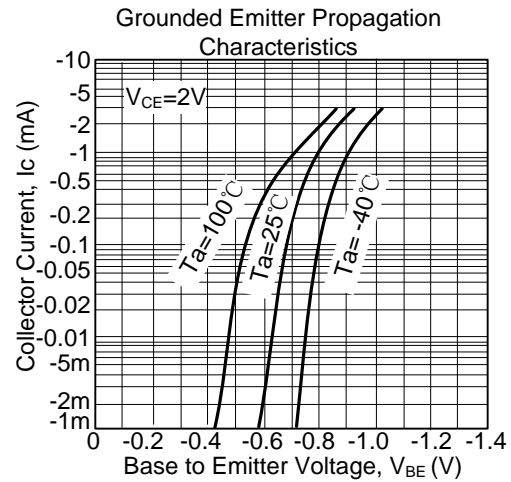
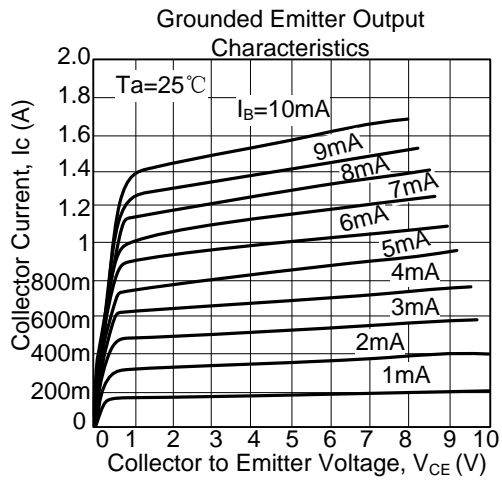
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = -50\mu A$	-50			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -1mA$	-50			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -50\mu A$	-6			V
Collector Cutoff Current	I_{CBO}	$V_{CB} = -50V$			-0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -5V$			-0.1	μA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C/I_B = -1A/-50mA$ (Note)		-0.15	-0.35	V
DC Current Gain	h_{FE}	$V_{CE} = -2V, I_C = -0.5A$ (Note)	120		400	
Transition Frequency	f_T	$V_{CE} = -2V, I_E = 0.5A, f = 100MHz$		200		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0A, f = 1MHz$		36		pF

Note: Measured using pulse current.

■ CLASSIFICATION OF h_{FE}

RANK	A	B
RANGE	120-240	200-400

TYPICAL CHARACTERISTICS



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